

INTEGRATION METHOD OF A SEMICONDUCTOR DEVICE HAVING A RECESSED
GATE ELECTRODE

ABSTRACT OF THE DISCLOSURE

5 Embodiments of the invention are directed to an integrated circuit device and a method for forming the device. In some embodiments of the invention, two types of transistors are formed on a single substrate, transistors: transistors having a recessed gate, and transistors having a planer gate electrode. In other embodiments, transistors having a recessed gate are formed in multiple areas of the same substrate. Additionally, gates of the
10 transistors in more than one region may be formed simultaneously.